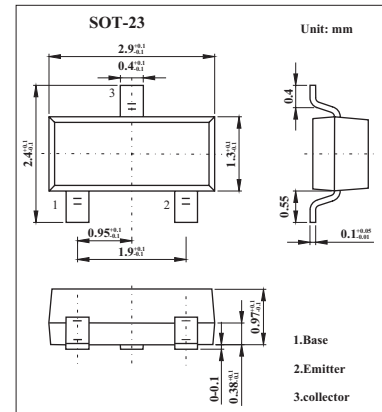


Silicon PNP Epitaxial Planar Type

2SC2406

■ Features

- Low noise voltage NV.
- High forward current transfer ratio hFE.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|-----------------------------|------------------|-------------|------|
| Collector-base voltage | V _{CB0} | 55 | V |
| Collector-emitter voltage | V _{CEO} | 55 | V |
| Emitter-base voltage | V _{EB0} | 5 | V |
| Collector current | I _c | 50 | mA |
| Peak collector current | I _{CP} | 100 | mA |
| Collector power dissipation | P _c | 200 | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|-----|------|
| Collector-base voltage | V _{CB0} | I _c = 10 μA, I _E = 0 | 55 | | | V |
| Collector-emitter voltage | V _{CEO} | I _c = 2 mA, I _B = 0 | 55 | | | V |
| Emitter-base voltage | V _{EB0} | I _E = 10 μA, I _c = 0 | 5 | | | V |
| Base-emitter voltage | V _{BE} | V _{CE} = 1 V, I _c = 100 mA | | 0.7 | 1.0 | V |
| Collector-base cutoff current | I _{CB0} | V _{CB} = 10 V, I _E = 0 | | | 0.1 | μA |
| Collector-emitter cutoff current | I _{CEO} | V _{CE} = 10 V, I _B = 0 | | | 1 | μA |
| Forward current transfer ratio | h _{FE} | V _{CE} = 5 V, I _c = 2 mA | 180 | | 700 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _c = 100 mA, I _B = -10 mA | | | 0.6 | V |
| Transition frequency | f _T | V _{CB} = 5 V, I _E = -2 mA, f = 200 MHz | | 200 | | MHz |
| Noise voltage | NV | V _{CE} = 10 V, I _c = 1 mA, G _v = 80 dB R _g = 100 kΩ, F _{function} = FLAT | | 110 | | mV |

■ hFE Classification

| Marking | TR | TS | TT |
|---------|---------|---------|---------|
| hFE | 180~360 | 260~520 | 360~700 |